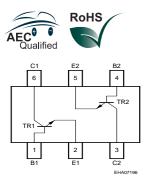


#### NPN Silicon RF Transistor\*

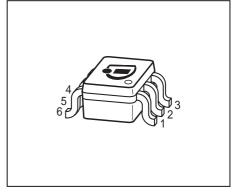
- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- $f_{\rm T}$  = 8 GHz, *F* = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated Transistor in one package
- For orientation in reel see package information below
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101
- \* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration				Package		
BFS483	RHs	1=B	2=E	3=C	4=B	5=E	6=C	SOT363

<sup>1</sup>Pb-containing package may be available upon special request





#### **Maximum Ratings**

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	12	V	
Collector-emitter voltage	V <sub>CES</sub>	20		
Collector-base voltage	V <sub>CBO</sub>	20		
Emitter-base voltage	V <sub>EBO</sub>	2		
Collector current	I <sub>C</sub>	65		
Base current	I <sub>B</sub>	5		
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	450	mW	
<i>T</i> <sub>S</sub> ≤ 40 °C				
Junction temperature	T <sub>i</sub>	150	°C	
Ambient temperature	T <sub>A</sub>	-65 150		
Storage temperature	T <sub>stq</sub>	-65 150		

# Thermal ResistanceParameterSymbolValueUnitJunction - soldering point2) $R_{thJS}$ $\leq 245$ K/W

#### **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	12	-	-	V
<i>I</i> <sub>C</sub> = 1 mA, <i>I</i> <sub>B</sub> = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	100	μA
<i>V</i> <sub>CE</sub> = 20 V, <i>V</i> <sub>BE</sub> = 0					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
V <sub>CB</sub> = 10 V, <i>I</i> <sub>E</sub> = 0					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	1	μA
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain-	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					

 ${}^{1}\mathcal{T}_{S}$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup>For calculation of  $R_{\rm thJA}$  please refer to Application Note Thermal Resistance



Parameter	Symbol		Values		
		min.	typ.	max.	
AC Characteristics (verified by random samplir	ng)	1	1	1	1
Transition frequency	f <sub>T</sub>	6	8	-	GHz
I <sub>C</sub> = 25 mA, V <sub>CE</sub> = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.34	0.54	pF
V <sub>CB</sub> = 10 V, <i>f</i> = 1 MHz, V <sub>BE</sub> = 0 ,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.13	-	
V <sub>CE</sub> = 10 V, <i>f</i> = 1 MHz, V <sub>BE</sub> = 0 ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	_	1.1	-	
V <sub>EB</sub> = 0.5 V, <i>f</i> = 1 MHz, V <sub>CB</sub> = 0 ,					
collector grounded					
Noise figure	F				dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
f = 900 MHz		-	0.9	-	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
f = 1.8 GHz		-	1.4	-	
Power gain, maximum stable <sup>1)</sup>	G <sub>ms</sub>	-	19	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 900 MHz					
Power gain, maximum available <sup>2)</sup>	G <sub>ma</sub>	-	12.5	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 1.8 GHz					
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω,					
f = 900 MHz		-	15.5	-	
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω,					
f = 1.8 MHz		-	10	-	

## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

 ${}^{1}G_{\rm ms} = |S_{21} / S_{12}|$ 

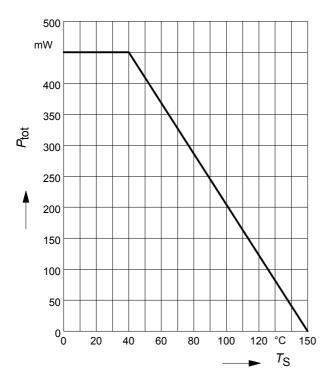
 ${}^{2}G_{\text{ma}} = |S_{21e} / S_{12e}| \ (k - (k^{2} - 1)^{1/2})$ 



**BFS483** 

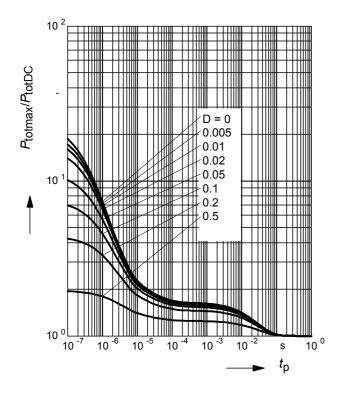
## Total power dissipation $P_{tot} = f(T_S)$

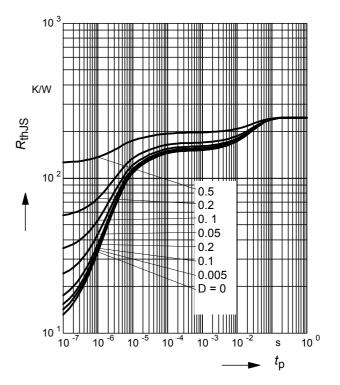
**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$ 



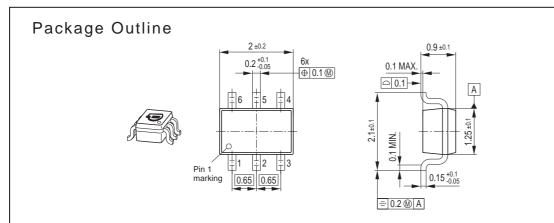
#### Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$ 

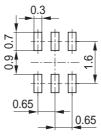






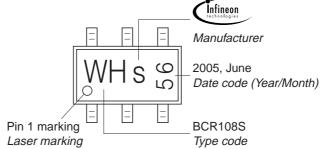


#### Foot Print



### Marking Layout (Example)

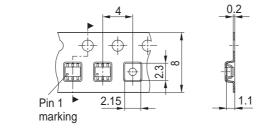
Small variations in positioning of Date code, Type code and Manufacture are possible.



#### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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